



NAND Flash Memories: an exciting IC design challenge

June 13th, 4PM (UTC+1), Magenta Seminar Room (D Floor)

[Zoom Link for remote connection](#)

Abstract: Memories are one of the major driving forces of the semiconductor industry; they accounted for over one quarter in sales over a total market of 416 B\$ in 2020 alone.

Semiconductor memory systems based on NAND Flash and DRAMs are everywhere around us (Personal Computers, Mobile Devices, Data Centers, ...) and will be among the key players in the emerging applications of the near future such as Internet of Things (IoT), Artificial Intelligence (AI) and mobility (autonomous driving).

Memories are subject to a relentless market push for increased density and performance, as well as reduced cost, thus they are at the frontline of technology and design innovation.

SK hynix, a world leader on semiconductor memory systems, will highlight some of the increasing challenges of multiple-bit-per-cell NAND flash memories.

The Company and the speakers : SK hynix Italy (SKHYIT) is SK hynix European R&D centre on NAND flash . Located near Milan, SKHYIT mission is to develop high density, high performance multiple-bits-per-cell flash memories in the state-of-art 3D NAND technology.



Jacopo Mulatti Born in 1967, MS degree in Electronic Engineering. Since 1995 he has worked on Flash Memory Design in STMicroelectronics, Numonyx and Micron Technologies. In 2014 he joined SK hynix as SKHYIT (SK hynix Italy) General Manager.



Marco Passerini Born in 1975, PhD degree in Electronic Engineering from University of Pavia. Since 2004 he has worked on Flash Memory Design in Atmel, Spansion, Elpida and SK hynix. In 2015 he became Analog Team Leader in SKHYIT (SK hynix Italy).

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